

TDA2822D

DUAL LOW-VOLTAGE POWER AMPLIFIER

SUPPLY VOLTAGE DOWN TO 1.8V

- LOWCROSSOVER DISTORTION
- LOW QUIESCENT CURRENT
- BRIDGE OR STEREO CONFIGURATION

DESCRIPTION

The TDA2822D is a monolithic integrated circuit in 8 lead (SO-8) package. It is intended for use as dual audio power amplifier in portable cassette players, radios and CD players



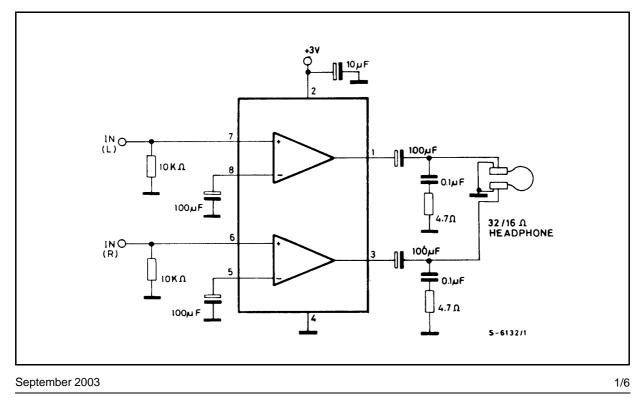
SO8

ORDERING NUMBER: TDA2822D

ABSOLUTE MAXIMUM RATINGS

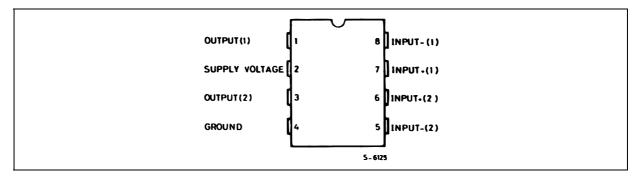
Symbol	Parameter	Value	Unit
Vs	Supply Voltage	15	V
lo	Peak Output	1	А
P _{tot}	Total Power Dissipation T _{amb} = 50°C	0.5	W
T _{stg} , T _j	Storage and Junction Temperature	-40 to 150	°C

APPLICATION CIRCUIT



TDA2822D

PIN CONNECTION (Top view)



THERMAL DATA

Symbol	I Description		Unit
R _{th j-amb}	Thermal Resistance Junction-ambient Max	200	°C/W

Figure 1: Stereo Application and Test Circuit

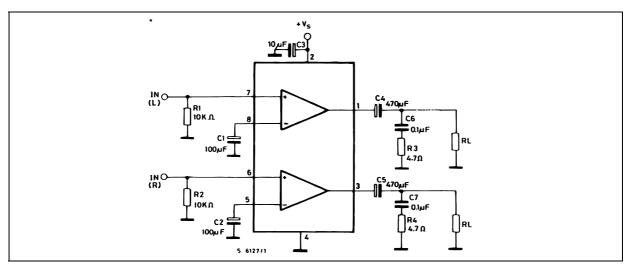
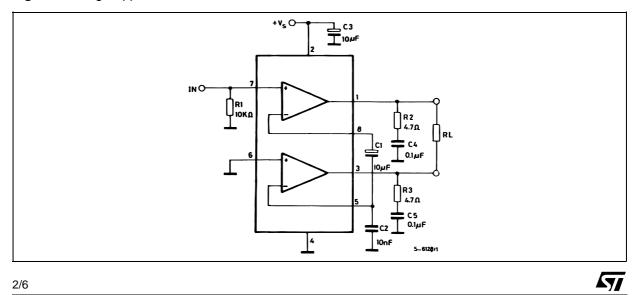


Figure 2: Bridge Application and Test Circuit



ELECTRICAL CHARACTERISTICS ($V_S = 6V$; $T_{amb} = 25^{\circ}C$, unless otherwise specified.

STEREO (Test circuit of fig. 1).

Symbol	Parameter	Test Condition		Min.	Тур.	Max.	Unit
Vs	Supply Voltage			1.8		15	V
l _d	Total Quiescent Drain Current					15	mA
Vo	Quiescent Output Voltage				2.7		V
		$V_S = 3V$			1.2		V
l _b	Input Bias Current				100		nA
Po	Output Power (each channel) (f = 1KHz, d = 10%)	$R_L = 32\Omega$	$V_{S} = 9V$ $V_{S} = 6V$ $V_{S} = 4.5V$ $V_{S} = 3V$ $V_{S} = 2V$		300 120 60 20 5		mW
		$R_L = 16\Omega$	$V_{\rm S} = 6V$	170	220		mW
		$R_L = 8\Omega$	$V_{S} = 6V$	300	380		mW
		$R_L = 4\Omega$	$V_S = 4.5V$ $V_S = 3V$		320 110		mW mW
d	Distortion	$R_L = 32\Omega$	$P_0 = 40 \text{mW}$		0.2		%
		$R_L = 16\Omega$	P _O = 75mW		0.2		%
		$R_L = 8\Omega$	P _O = 150mW		0.2		%
Gv	Closed Loop Voltage Gain	f = 1KHz		36	39	41	dB
ΔG_V	Channel Balance					±1	dB
Ri	Input Resistance	f = 1KHz		100			KΩ
e _N	Total Input Noise	$R_s = 10k\Omega$	B = Curve A		2		μV
		$R_s = 10k\Omega$	B = 22Hz to 22KHz		2.5		μV
SVR	Supply Voltage Rejection	f = 100Hz	$C1 = C2 = 100 \mu F$	24	30		dB
Cs	Channel Separation	f = 1KHz			50		dB

BRIDGE (Test circuit of fig.2)

Vs	Supply Voltage		1.8		15	V
I _d	Total Quiescent Drain Current	R _L = ∞			15	mA
Vos	Output Offset Voltage (between the outputs)	$R_L = 8\Omega$			±80	mV
lb	Input Bias Current			100		nA
Po	Output Power (f = 1KHz, d = 10%)	$R_{L} = 32\Omega \qquad \begin{array}{c} V_{S} = 9V \\ V_{S} = 6V \\ V_{S} = 4.5V \\ V_{S} = 3V \\ V_{S} = 2V \end{array}$	320 50	1000 400 200 65 8		mW
		$\begin{array}{c c} R_L = 16\Omega & V_S = 6V \\ V_S = 3V \end{array}$		800 120		mW mW
		$\begin{array}{ll} R_L = 8\Omega & V_S = 4.5V \\ V_S = 3V \end{array}$		700 220		mW mW
		$\begin{array}{c} R_L = 4\Omega & V_S = 3V \\ V_S = 2V \end{array}$		350 80		mW mW
d	Distortion	$R_{L} = 8\Omega P_{O} = 0.5W f =$	1KHz	0.2		%
Gv	Closed Loop Voltage Gain	f = 1KHz		39		dB
Ri	Input Resistance	f = 1KHz	100			KΩ
e _N	Total Input Noise	$R_s = 10k\Omega$ B = Curve A		2.5		μV
		$R_s = 10k\Omega$ B = 22Hz to	22KHz	3		μV
SVR	Supply Voltage Rejection	f = 100Hz		40		dB
В	Power Bandwidth (-3dB)	$R_L = 8\Omega$ $P_O = 1W$		120		KHz



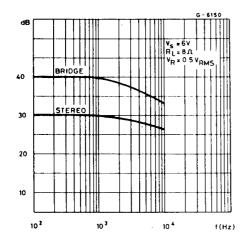
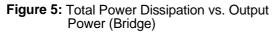


Figure 3: Supply Voltage Rejection vs. Frequency



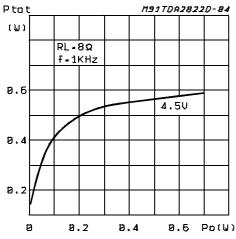
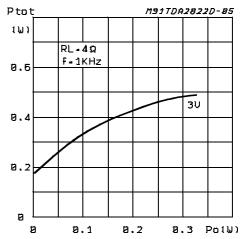


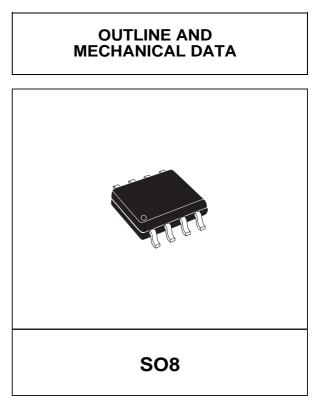
Figure 4: Output Power vs. Supply Voltage (THD = 10%, f = 1KHz Stereo) Pa (W) B.B B.6 B.4 RL-4Ω RL-4Ω RL-8Ω B.2 2 3 4 5 6 Us(U)

Figure 6: Total Power Dissipation vs. Output Power (Bridge)

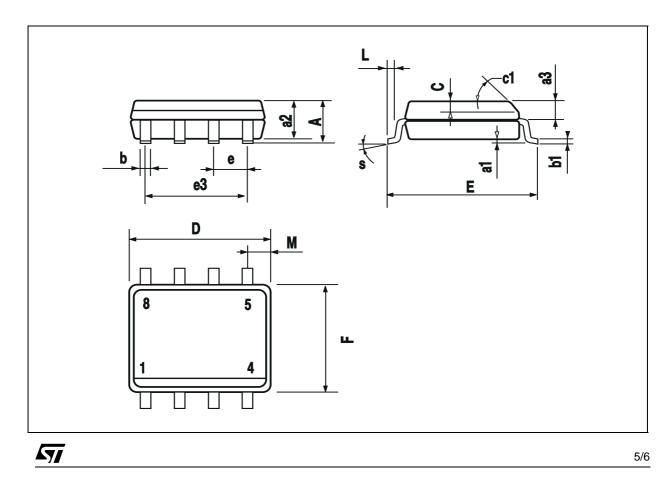


5

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			1.75			0.069	
a1	0.1		0.25	0.004		0.010	
a2			1.65			0.065	
a3	0.65		0.85	0.026		0.033	
b	0.35		0.48	0.014		0.019	
b1	0.19		0.25	0.007		0.010	
С	0.25		0.5	0.010		0.020	
c1			45° ((typ.)			
D (1)	4.8		5.0	0.189		0.197	
Е	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		3.81			0.150		
F (1)	3.8		4.0	0.15		0.157	
L	0.4		1.27	0.016		0.050	
М			0.6			0.024	
S	8° (max.)						



 D and F do not include mold flash or protrusions. Mold flash or potrusions shall not exceed 0.15mm (.006inch).



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2003 STMicroelectronics - All rights reserved

STMicroelectronics GROUP OF COMPANIES

Australia – Belgium - Brazil - Canada - China – Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States

www.st.com

47

6/6